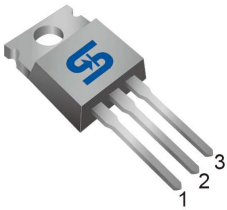
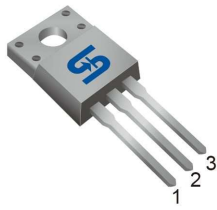


TO-220



ITO-220



Pin Definition:

1. Gate
2. Drain
3. Source

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
800	3 @ $V_{GS}=10V$	4

General Description

The TSM4N80 N-Channel enhancement mode Power MOSFET is produced by planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply, electronic lamp ballast based on half bridge.

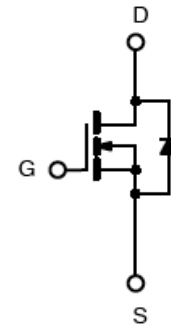
Features

- Low $R_{DS(on)}$ 3 Ω (Max.)
- Low gate charge typical @ 25nC (Typ.)
- Improve dv/dt capability

Ordering Information

Part No.	Package	Packing
TSM4N80CZ C0	TO-220	50pcs / Tube
TSM4N80CI C0	ITO-220	50pcs / Tube

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	TO-220	ITO-220	Unit
Drain-Source Voltage	V_{DS}	800		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current	I_D	4	4 *	A
		2.5	2.5 *	
Pulsed Drain Current *	I_{DM}	16	16 *	A
Peak Diode Recovery dv/dt (Note 3)	dv/dt	4.5		V
Single Pulse Avalanche Energy (Note 2)	E_{AS}	85		mJ
Avalanche Current (Repetitive) (Note 1)	I_{AR}	4		A
Repetitive Avalanche Energy (Note 1)	E_{AR}	12.3		mJ
Power Dissipation	P_D	123	38.7	W
		0.98	0.3	$^\circ\text{C/W}$
Operating Junction Temperature	T_J	150		$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to +150		$^\circ\text{C}$

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	TO-220	ITO-220	Unit
Thermal Resistance - Junction to Case	$R\theta_{JC}$	1.01	3.23	$^{\circ}\text{C/W}$
Thermal Resistance - Junction to Ambient	$R\theta_{JA}$	62.5		

Notes: Surface mounted on FR4 board $t \leq 10\text{sec}$

Electrical Specifications ($T_c = 25^{\circ}\text{C}$ unless otherwise noted)

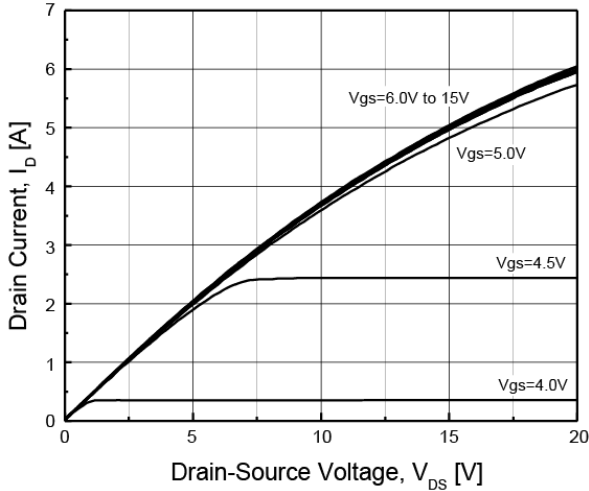
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV_{DSS}	800	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 2.0A$	$R_{DS(ON)}$	--	2.5	3.0	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	$V_{GS(TH)}$	2.0	--	4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 800V, V_{GS} = 0V$	I_{DSS}	--	--	10	μA
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Forward Transconductance	$V_{DS} = 30V, I_D = 2.0A$	g_{fs}	--	7.1	--	S
Diode Forward Voltage	$I_S = 4A, V_{GS} = 0V$	V_{SD}	--	--	1.5	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 640V, I_D = 4A, V_{GS} = 10V$	Q_g	--	20	--	nC
Gate-Source Charge		Q_{gs}	--	3.7	--	
Gate-Drain Charge		Q_{gd}	--	8.2	--	
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	C_{iss}	--	955	--	pF
Output Capacitance		C_{oss}	--	80	--	
Reverse Transfer Capacitance		C_{rss}	--	13	--	
Switching ^c						
Turn-On Delay Time	$V_{GS} = 10V, I_D = 4A, V_{DD} = 400V, R_G = 25\Omega$	$t_{d(on)}$	--	49	--	nS
Turn-On Rise Time		t_r	--	38	--	
Turn-Off Delay Time		$t_{d(off)}$	--	146	--	
Turn-Off Fall Time		t_f	--	50	--	
Reverse Recovery Time	$V_{GS} = 0V, I_S = 4A,$	t_{fr}	--	487	--	nS
Reverse Recovery Charge	$di_F/dt = 100A/\mu s$	Q_{fr}	--	2.8	--	μC

Notes:

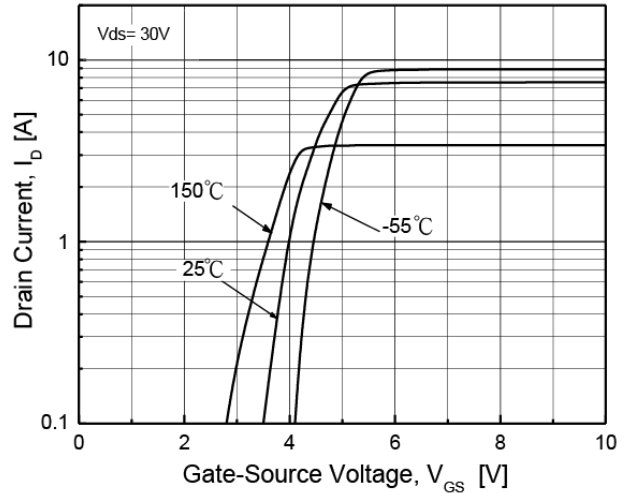
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. $V_{DD} = 50\text{V}, I_{AS} = 4\text{A}, L = 10\text{mH}, R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. $I_{SD} \leq 8\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV$, Starting $T_J = 25^{\circ}\text{C}$
4. Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
5. b For design reference only, not subject to production testing.
6. c Switching time is essentially independent of operating temperature.

Electrical Characteristics Curve (Tc = 25°C, unless otherwise noted)

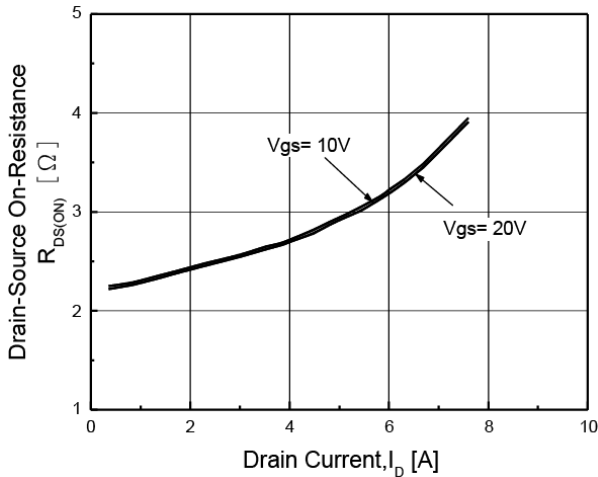
Output Characteristics



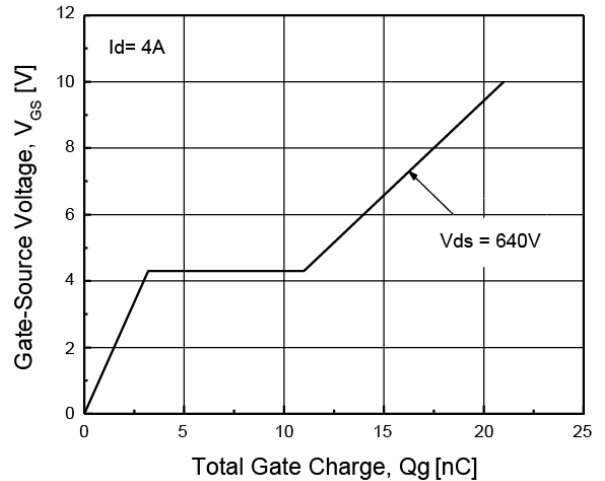
Transfer Characteristics



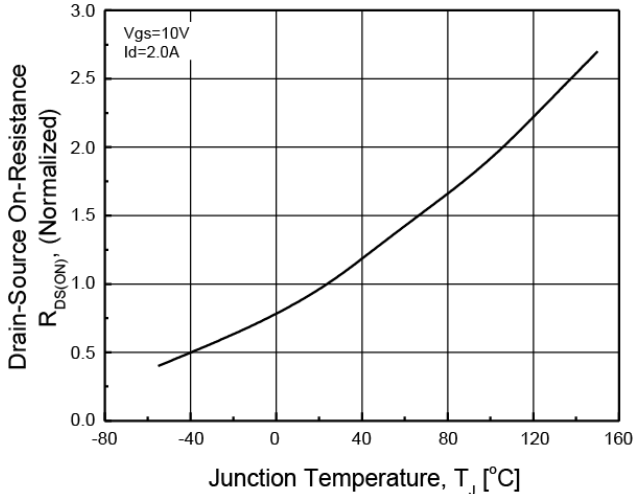
On-Resistance vs. Drain Current



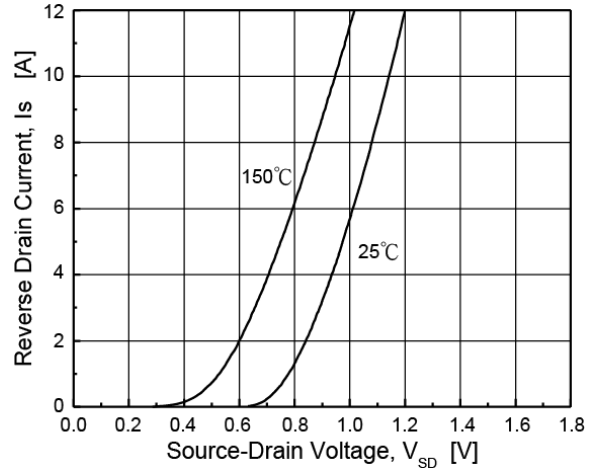
Gate Charge



On-Resistance vs. Junction Temperature

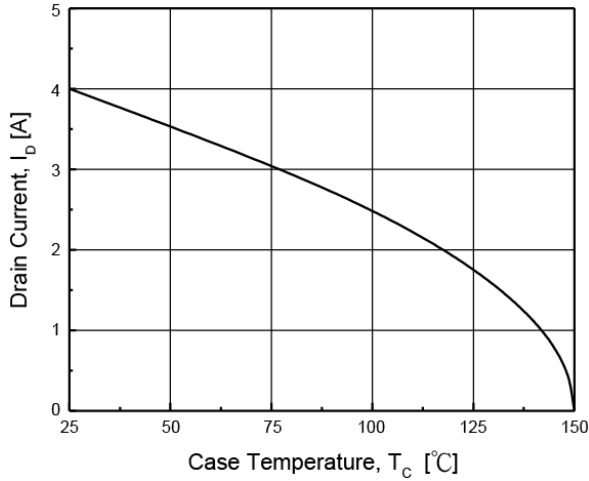


Source-Drain Diode Forward Voltage

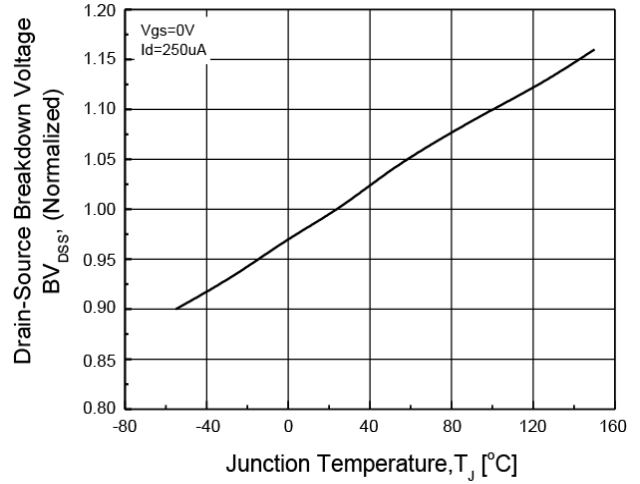


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

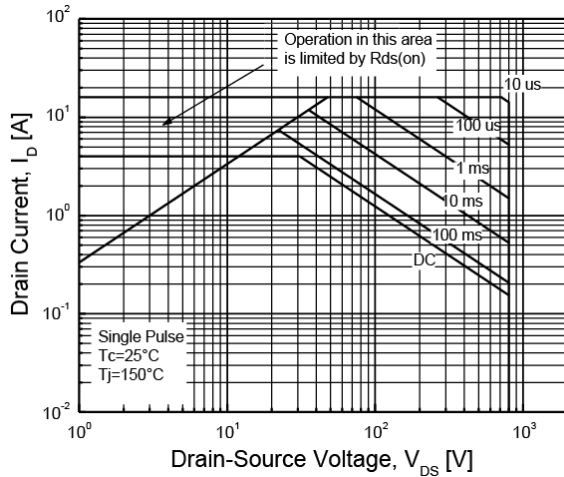
Drain Current vs. Case Temperature



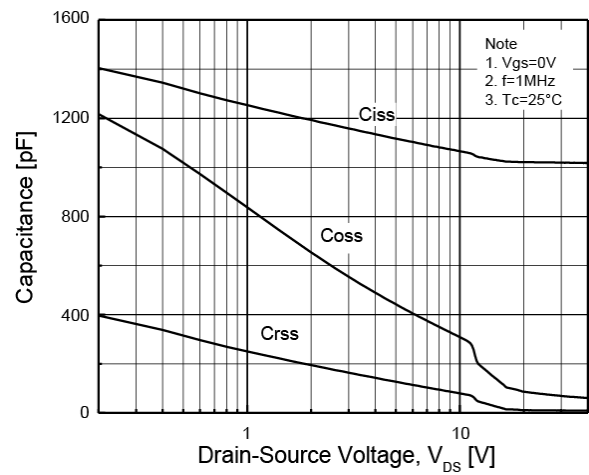
BV_{DSS} vs. Junction Temperature



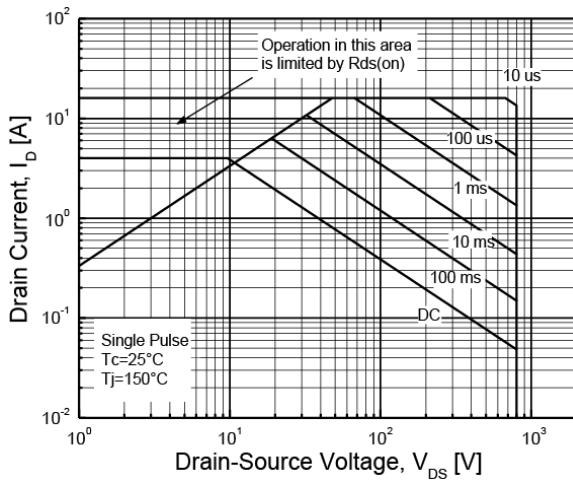
Maximum Safe Operating Area (TO-220)



Capacitance vs. Drain-Source Voltage

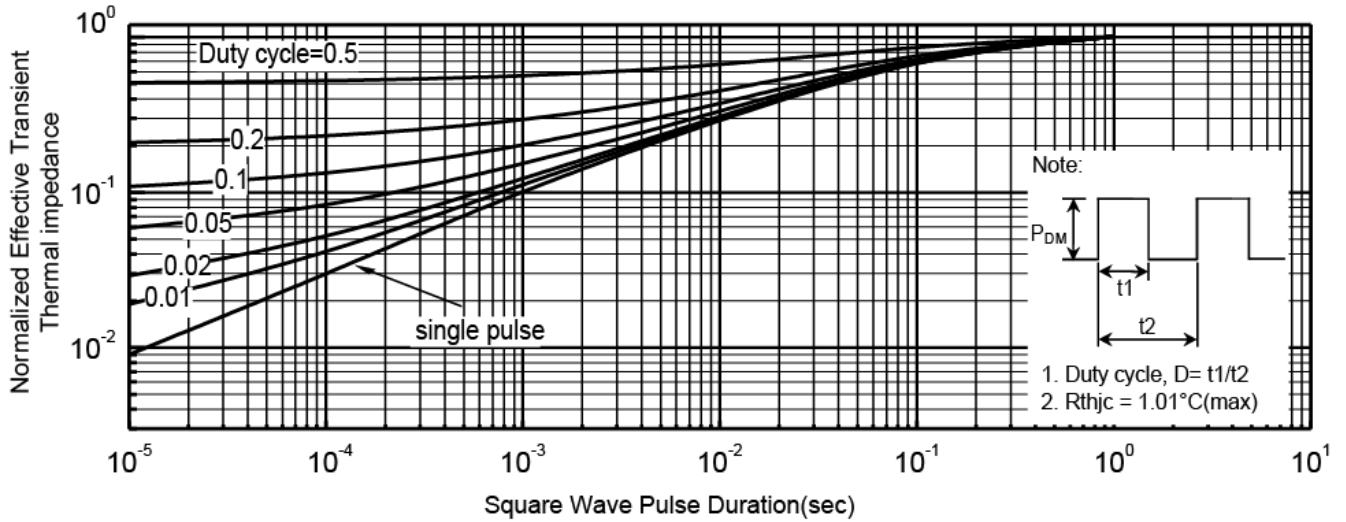


Maximum Safe Operating Area (ITO-220)

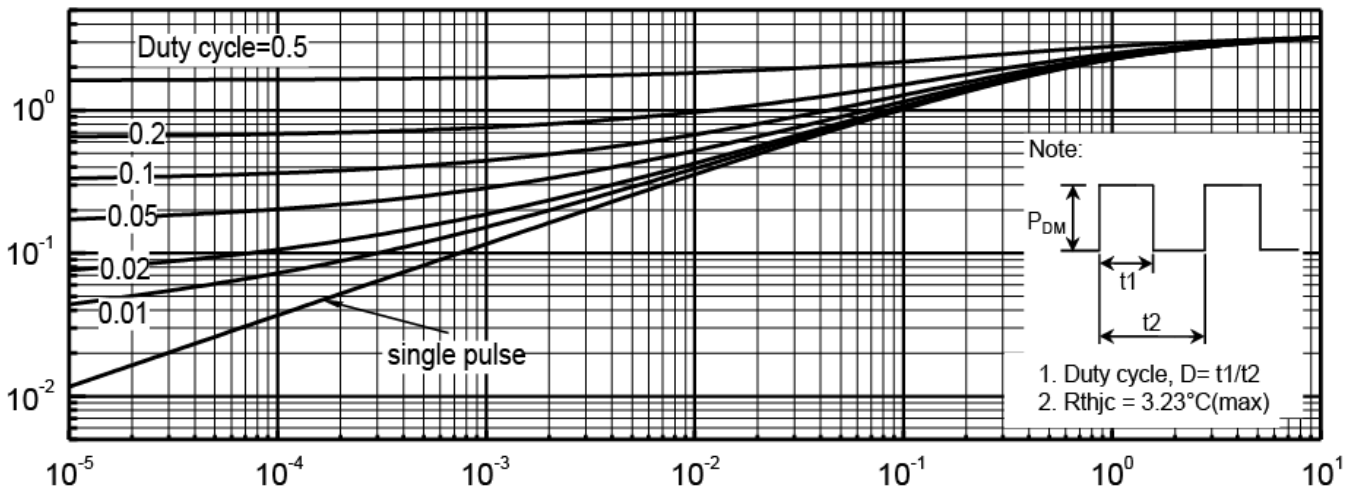


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

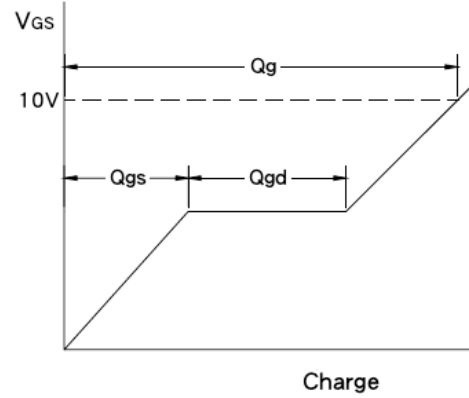
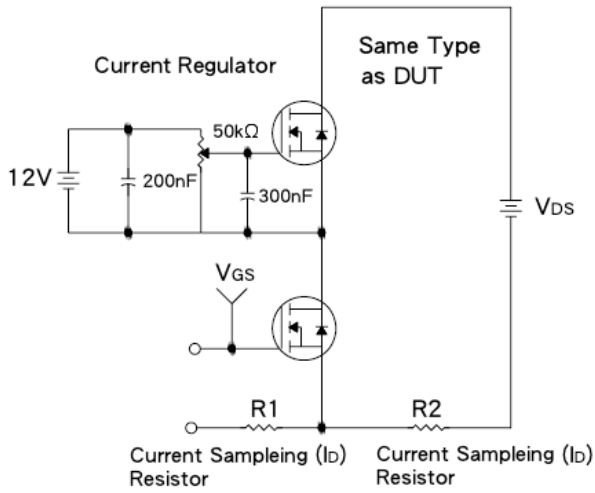
Normalized Thermal Transient Impedance, Junction-to-Ambient



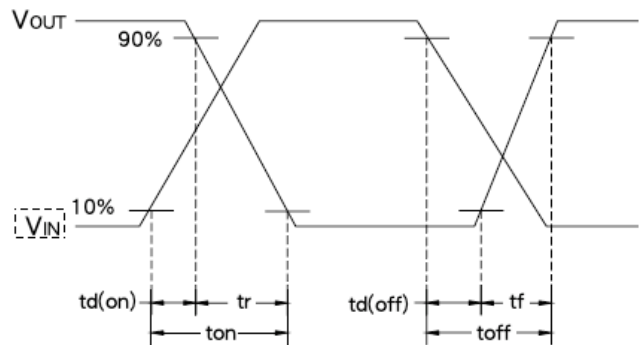
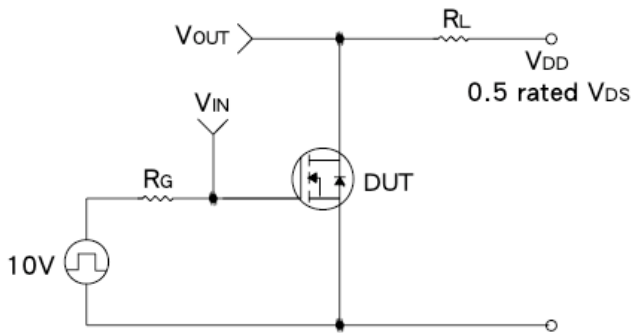
Normalized Thermal Transient Impedance, Junction-to-Ambient(ITO-220)



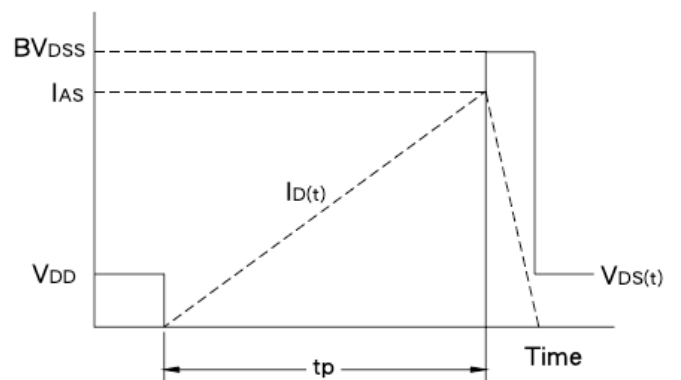
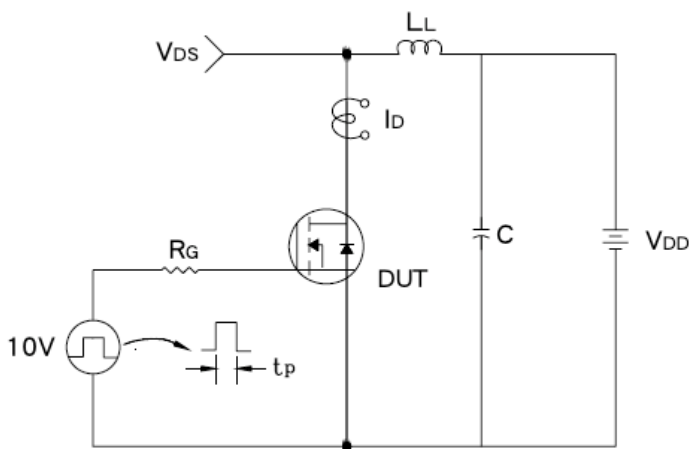
Gate Charge Test Circuit & Waveform



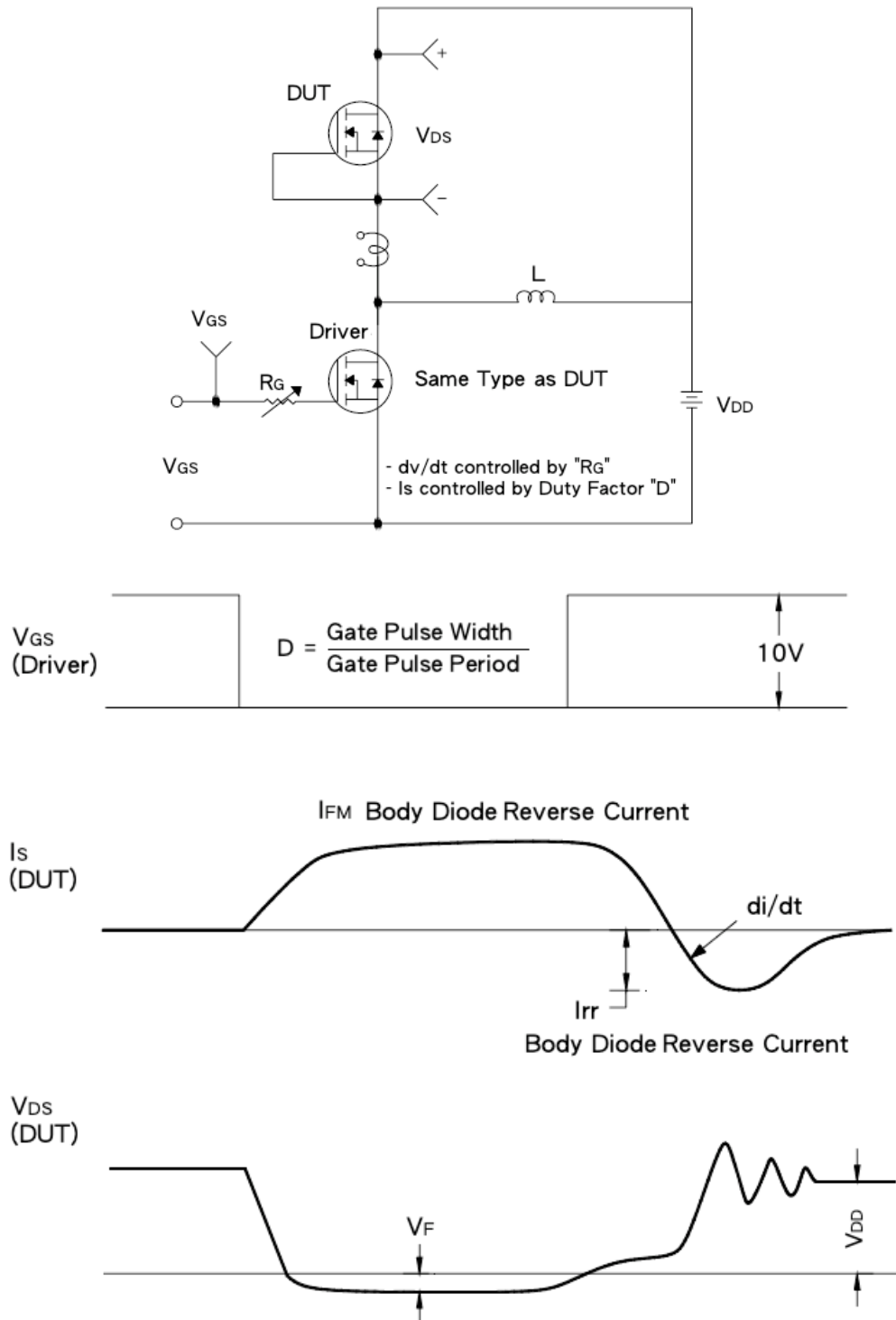
Resistive Switching Test Circuit & Waveform



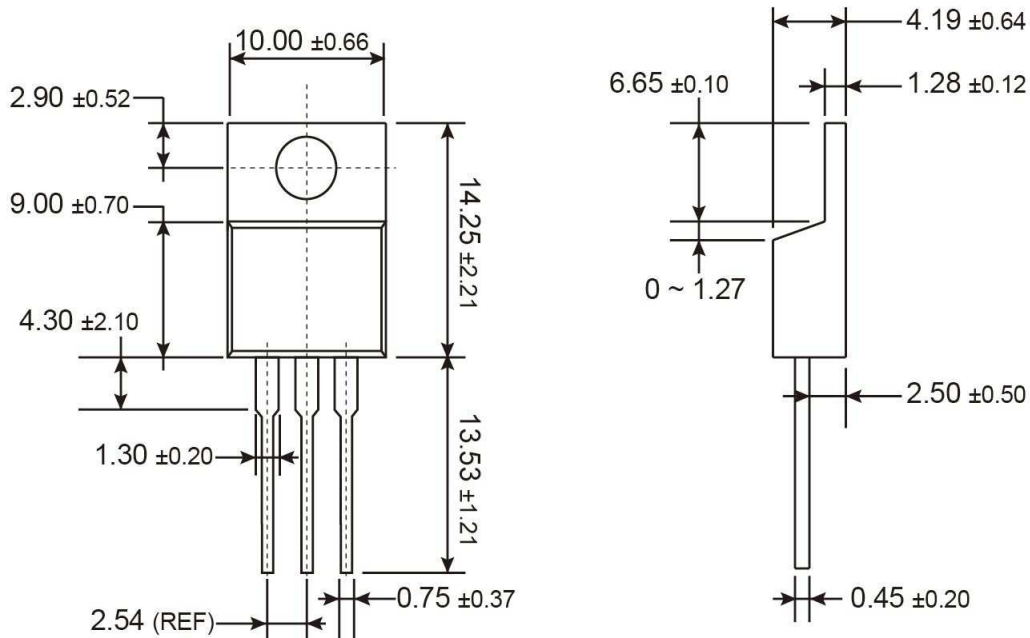
E_{AS} Test Circuit & Waveform



Diode Reverse Recovery Time Test Circuit & Waveform

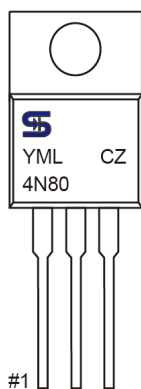


TO-220 Mechanical Drawing



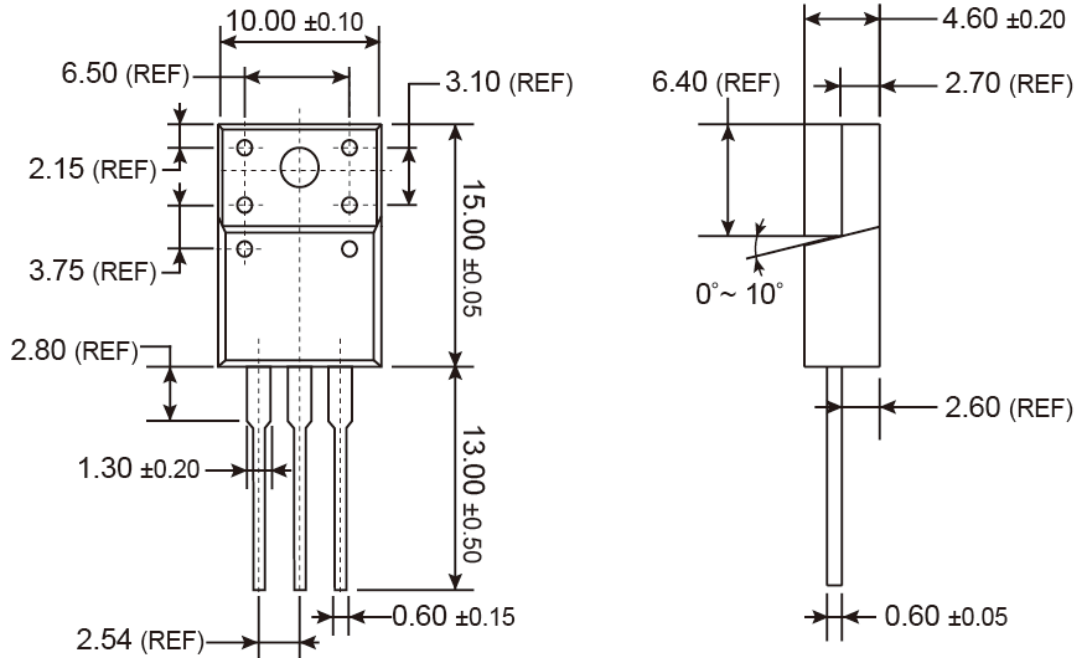
Unit: Millimeters

Marking Diagram



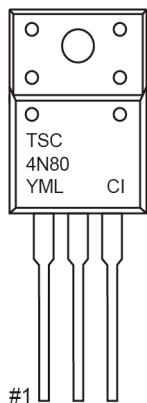
- Y** = Year Code
- M** = Month Code
 - (**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apr, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)
- L** = Lot Code

ITO-220 Mechanical Drawing



Unit: Millimeters

Marking Diagram



- Y** = Year Code
- M** = Month Code
 - (**A**=Jan, **B**=Feb, **C**=Mar, **D**=Apr, **E**=May, **F**=Jun, **G**=Jul, **H**=Aug, **I**=Sep, **J**=Oct, **K**=Nov, **L**=Dec)
- L** = Lot Code

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf, assumes no responsibility or liability for any errors or inaccuracies.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.

Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



Тел: +7 (812) 336 43 04 (многоканальный)

Email: org@lifeelectronics.ru

www.lifeelectronics.ru